

Structure of Nonvolatile Memory Array

ABSTRACT OF THE INVENTION

5 A structure of a nonvolatile memory array with low source
line sheet resistance is disclosed in this present invention. The key
aspect of this present invention is employing a buried conductive
region as the source line of a nonvolatile memory array. The topology
of the above-mentioned buried conductive region is different from the
10 source line in the prior art. Therefore, this invention can provide a
nonvolatile memory array for reducing the source line sheet
resistance and achieving the reliability and the operating performance
of the nonvolatile memory array.